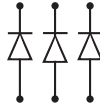


CMKSH-3T
SURFACE MOUNT
ULTRAmi™
TRIPLE ISOLATED
SILICON SCHOTTKY DIODES

ULTRAmi™



SOT-363 CASE

Central™
Semiconductor Corp.

DESCRIPTION:

The CENTRAL SEMICONDUCTOR CMKSH-3T type contains three (3) Isolated Silicon Schottky Diodes, epoxy molded in a SOT-363 surface mount package. This ULTRAmi™ device has been designed for switching applications requiring a low forward voltage drop.

MARKING CODE: KHT

MAXIMUM RATINGS: ($T_A=25^{\circ}\text{C}$)

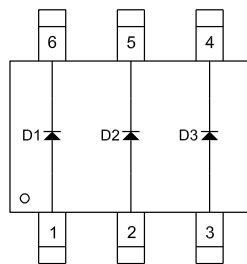
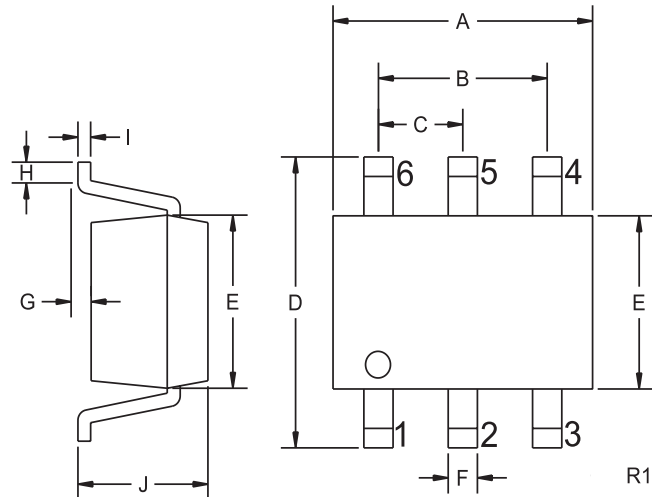
	SYMBOL		UNITS
Peak Repetitive Reverse Voltage	V_{RRM}	30	V
Continuous Forward Current	I_F	100	mA
Peak Repetitive Forward Voltage	I_{FRM}	350	mA
Forward Surge Current, $t_p=10\text{ms}$	I_{FSM}	750	mA
Power Dissipation	P_D	350	mW
Operating and Storage			
Junction Temperature	T_J, T_{stg}	-65 to +150	$^{\circ}\text{C}$
Thermal Resistance	Θ_{JA}	357	$^{\circ}\text{C/W}$

ELECTRICAL CHARACTERISTICS PER DIODE: ($T_A=25^{\circ}\text{C}$ unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNITS
B_{VR}	$I_R=100\mu\text{A}$	30			V
V_F	$I_F=2.0\text{mA}$		0.29	0.33	V
V_F	$I_F=15\text{mA}$		0.40	0.45	V
V_F	$I_F=100\text{mA}$		0.74	1.00	V
I_R	$V_R=25\text{V}$		90	500	nA
I_R	$V_R=25\text{V}, T_A=100^{\circ}\text{C}$		25	100	μA
C_T	$V_R=1.0\text{V}, f=1\text{ MHz}$		7.0		pF
t_{rr}	$I_F=I_R=10\text{mA}, I_{rr}=1.0\text{mA}, R_L=100\Omega$			5.0	ns

R2 (7-August 2003)

SOT-363 CASE - MECHANICAL OUTLINE



LEAD CODE:

- 1) ANODE D1
- 2) ANODE D2
- 3) ANODE D3
- 4) CATHODE D3
- 5) CATHODE D2
- 6) CATHODE D1

MARKING CODE: KHT

DIMENSIONS				
SYMBOL	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.073	0.085	1.85	2.15
B	0.051		1.30	
C	0.026		0.65	
D	0.075	0.091	1.90	2.30
E	0.043	0.055	1.10	1.40
F	0.006	0.012	0.15	0.30
G	0.000	0.004	0.00	0.10
H	0.010	-	0.25	-
I	0.004	0.010	0.10	0.25
J	0.031	0.039	0.80	1.00

SOT-363 (REV: R1)

R2 (7-August 2003)